

	Type	L #	Hits	Search Text	DBs	Comments
1	BRS	L1	15327 2	438/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
2	BRS	L2	24	1 and (p-channel near (flash or non-volatile or memeory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
3	BRS	L3	1	2 and ((tunnel near (oxide or dielectric)) near thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
4	BRS	L4	641	forbes-leonard.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
5	BRS	L5	20	4 and ((p-channel or (depletion near mode)) near (flash or non-volatile or memeory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
6	BRS	L6	13	5 and ((tunnel near (oxide or dielectric)) near thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
7	BRS	L7	487	(tunnel near (oxide or dielectric)).ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
8	BRS	L8	3	7 and (p-channel near (flash or non-volatile or memeory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
9	BRS	L9	101	((p-channel or (depletion near mode)) near (flash or non-volatile or memeory))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
10	BRS	L10	21	9 and ((tunnel near (oxide or dielectric)) near thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
11	BRS	L11	765	((tunnel near (oxide or dielectric)) near thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
12	BRS	L12	12	thin near ((tunnel near (oxide or dielectric)) near thickness)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	
13	BRS	L13	4	10 and fixed near charge	USPAT	